

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Currently Amended) A method for manufacturing a semiconductor comprising:

~~forming a plurality of electrodes on a semiconductor element;~~

~~— applying a layer of a resin to the semiconductor element in a region of the element that does not include the electrodes, the layer of resin being applied such that a height of the layer is greater than a height of the electrodes;~~

~~— forming a conductive layer over the plurality of electrodes and the layer of resin;~~

~~— patterning the conductive layer on the electrodes and the layer of the resin in a predetermined pattern; and~~

~~removing portions of the layer of resin by using the patterned conductive layer as a mask so that remaining portions of the layer of resin form a plurality of protrusions.~~

forming a first conductive layer by electroless nickel plating on the plurality of the electrodes before applying a layer of a resin in a subsequent step;

applying the layer of the resin to the semiconductor element in a region of the semiconductor element that does not include the electrodes, the layer of the resin being applied such that a height of the layer of the resin is greater than a height of the electrodes;

forming a second conductive layer over the plurality of the electrodes and the layer of the resin, the second conductive layer being connected to the first conductive layer and covering a top surface of the layer of the resin;

patterning the second conductive layer on the electrodes and the layer of the resin in a predetermined pattern; and

removing portions of the layer of the resin using the patterned second conductive layer as a mask so that remaining portions of the layer of the resin form a plurality of protrusions.

2. (Original) The method for manufacturing a semiconductor device according to Claim 1, wherein the layer of the resin is removed by plasma processing.

3. (Currently Amended) The method for manufacturing a semiconductor device according to Claim 1, wherein the second conductive layer is formed by sputtering.

4. (Currently Amended) The method for manufacturing a semiconductor device according to Claim 1, wherein the second conductive layer is formed by plating.

5–13. (Cancelled)